

first layer 82, or alternatively or additionally, layer 82 may be polished so as to serve as a reflecting surface. --

Please replace the paragraph beginning at page 38, line 14, with the following rewritten paragraph:

-- The mirror was constructed of a silicon wafer, polished on both sides, whose front (mirror) side was evaporated with a reflective layer and the wafer was annealed at 450 °C for approximately 30 minutes. 1" or 2" n-type wafers were used, with a diameter of the porous area of 0.5" and 1". The back side of the wafer was made porous by etching in HF:ethanol (1:1) solution, with the HF itself dissolved in water (1:1). --

In the Drawings:

In Fig. 5, please correct Fig. 5 according to the 'red' correction markings.

In the Claims:

Please amend claim 1 as follows:

1. (Amended) A piezoelectric device comprising a first element of porous crystalline material, a second element being attached to, or integrally formed with, said first element, and at least one electrode being in electrical contact solely with said first element of said first and second elements, such that subjecting said first element to an electric potential via said at least one electrode results in a strain induced by said first element on said second element.

Please amend claim 2 as follows:

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